

SANYO Semiconductors DATA SHEET

FSS145 — General-Purpose Switching Device Applications

Features

- · Load switching applications.
- · Low ON-resistance.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-45	٧
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ΙD		-8	Α
Drain Current (PW≤10s)	ID	Duty cycle≤1%	-8.5	Α
Drain Current (PW≤10μs)	IDP	Duty cycle≤1%	-32	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (1200mm ² X0.8mm), PW≤10s	2.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			11-2
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-45			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-45V, V _{GS} =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	VGS=±16V, VDS=0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-8A	10	17		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-8A, VGS=-10V		18	24	mΩ
	R _{DS} (on)2	I _D =-4A, V _G S=-4V		28	40	mΩ
Input Capacitance	Ciss	V _{DS} =-20V, f=1MHz		3490		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		370		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-20V, f=1MHz		290		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		35		ns
Rise Time	tr	See specified Test Circuit.		65		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		270		ns
Fall Time	t _f	See specified Test Circuit.		125		ns

Marking: S145 Continued on next page.

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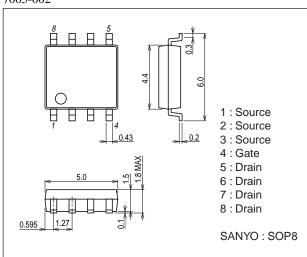
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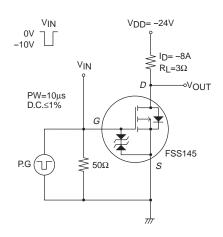
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	l oill
Total Gate Charge	Qg	V _{DS} =-24V, V _{GS} =-10V, I _D =-8A		63		nC
Gate-to-Source Charge	Qgs	V _{DS} =-24V, V _{GS} =-10V, I _D =-8A		9		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-24V, V _{GS} =-10V, I _D =-8A		12		nC
Diode Forward Voltage	VSD	IS=-8A, VGS=0V		-0.81	-1.5	V

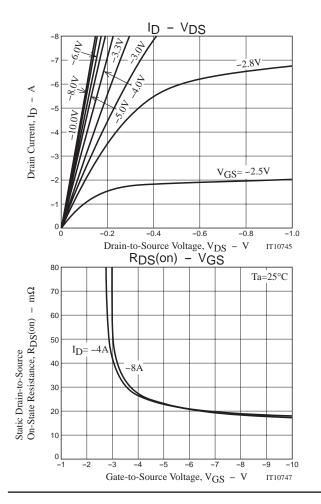
Package Dimensions

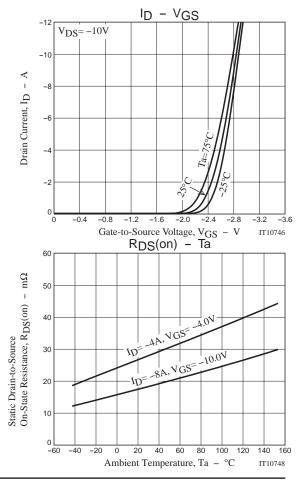
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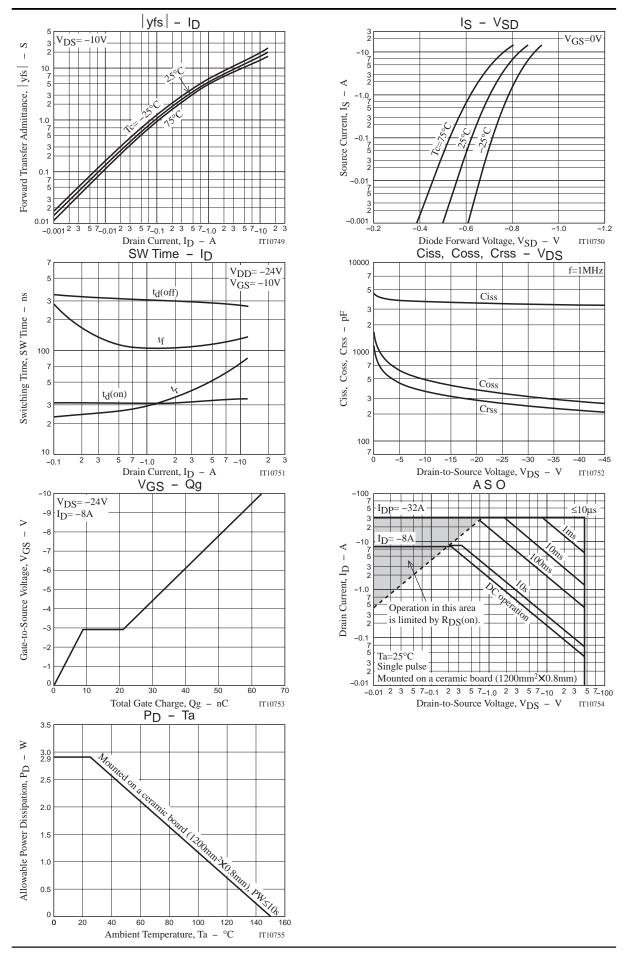


Switching Time Test Circuit









Note on usage: Since the FSS145 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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